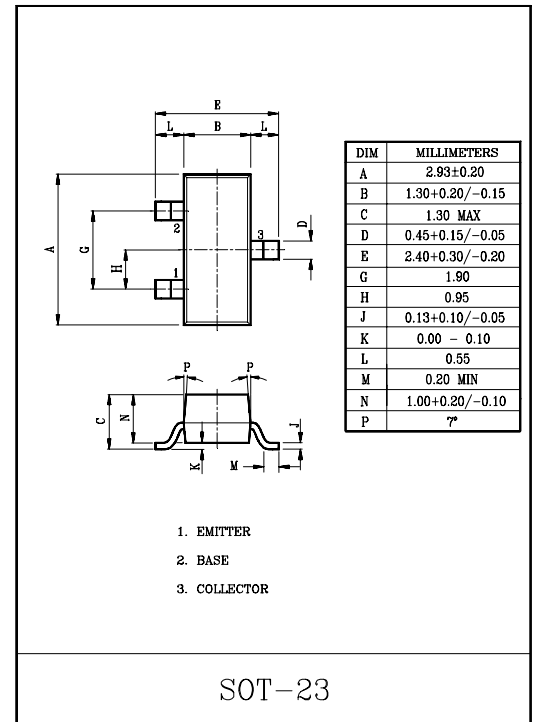


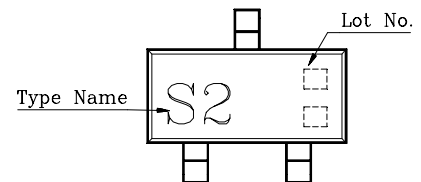
HIGH FREQUENCY APPLICATION.
VHF BAND AMPLIFIER APPLICATION.

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	30	V
Collector-Emitter Voltage	V _{CEO}	15	V
Emitter-Base Voltage	V _{EBO}	3	V
Collector Current	I _C	100	mA
Emitter Current	I _E	-100	mA
Collector Power Dissipation	P _C	200	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-65~150	°C



Marking



ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C =3mA, I _B =0	15	-	-	V
Collector-Base Breakdown Voltage	V _{(BR)CBO}	I _C =1μA, I _E =0	30	-	-	V
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I _E =10μA, I _C =0	3.0	-	-	V
Collector Cut-off Current	I _{CBO}	V _{CB} =15V, I _E =0	-	-	10	nA
DC Current Gain	h _{FE}	V _{CE} =1V, I _C =3mA	20	-	-	
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C =10mA, I _B =1mA	-	-	1.0	V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =10mA, I _B =1mA	-	-	0.4	V
Transition Frequency	f _T	I _C =4mA, V _{CE} =10V, f=100MHz	600	-	-	MHz
Collector Input Capacitance	C _{ib}	V _{EB} =0.5V, I _C =0, f=1MHz	-	-	2.0	pF
Collector Output Capacitance	C _{ob}	V _{CB} =0V, I _E =0, f=1MHz	-	-	3.0	pF
		V _{CB} =10V, I _E =0, f=1MHz	-	-	1.7	
Noise Figure	NF	V _{CE} =6V, I _C =1mA, R _g =400Ω, f=60MHz	-	-	6.0	dB